YEA SHIN TECHNOLOGY CO., LTD

YSE2219ZDW

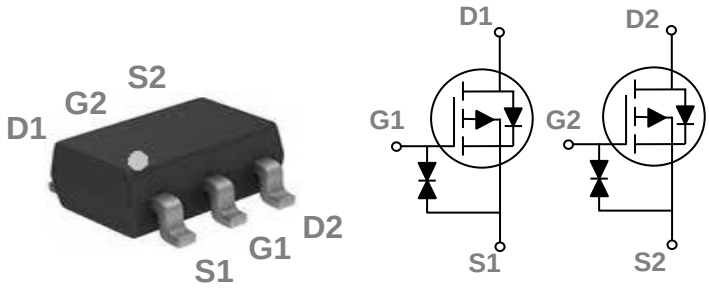
Dual P-Channel Enhancement MOSFET

VDS= -20V, ID= -540mA

Features

- *Fast switching*
- *Green Device Available*
- *Suit for 1.5V Gate Drive Applications*

SOT-363 Dual Pin Configuration



Applications

- *Notebook*
- *Load Switch*
- *Networking*
- *Hand-held Instruments*

Absolute Maximum Rating T_C=25℃ **unless otherwise noted**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±8	V
I_D	Drain Current – Continuous (T_A=25℃)	-540	mA
	Drain Current – Continuous (T_A=70℃)	-430	mA
I_{DM}	Drain Current – Pulsed[1]	-2.16	A
P_D	Power Dissipation (T_A=25℃)	278	mW
	Power Dissipation – Derate above 25℃	2.2	mW/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	450	℃/W

DEVICE CHARACTERISTICS

YSE2219ZDW

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=-1mA	---	-0.01	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V, V_{GS}=0V, T_J=25℃	---	---	-1	uA
		V_{DS}=-16V, V_{GS}=0V, T_J=125℃	---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±8V, V_{DS}=0V	---	---	±20	uA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance	V_{GS}=-4.5V, I_D=-0.3A	---	440	600	mΩ
		V_{GS}=-2.5V, I_D=-0.2A	---	610	850	mΩ
		V_{GS}=-1.8V, I_D=-0.1A	---	810	1200	mΩ
		V_{GS}=-1.5V, I_D=-0.1A	---	1020	1600	mΩ
		V_{GS}=-1.2V, I_D=-0.1A	---	1800	3000	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS}, I_D=-250uA	-0.3	-0.6	-1	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	3	---	mV/℃

Dynamic and Switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=-10V, V_{GS}=-4.5V, I_D=-0.2A	---	1	2	nC
Q_{gs}	Gate-Source Charge[2,3]		---	0.28	0.5	
Q_{gd}	Gate-Drain Charge[2,3]		---	0.18	0.4	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=-10V, V_{GS}=-4.5V, R_G=10Ω, I_D=-0.2A	---	8	16	ns
T_r	Rise Time[2,3]		---	5.2	10	
$T_{d(off)}$	Turn-On Delay Time[2,3]		---	30	60	
T_f	Fall Time[2,3]		---	18	36	
C_{iss}	Input Capacitance	V_{DS}=-10V, V_{GS}=0V, f=1MHz	---	40	78	pF
C_{oss}	Output Capacitance		---	15	30	
C_{rss}	Reverse Transfer Capacitance		---	6.5	13	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V, Force Current	---	---	-0.54	A
I_{SM}	Pulsed Source Current		---	---	-1.08	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=-0.2A, T_J=25℃	---	---	-1	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

DEVICE CHARACTERISTICS

YSE2219ZDW

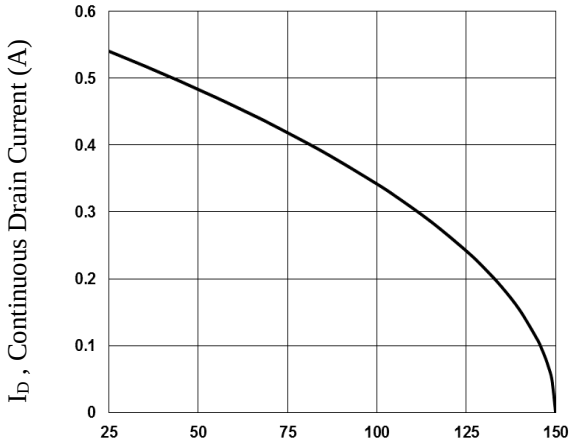


Fig.1 Continuous Drain Current vs. T_C

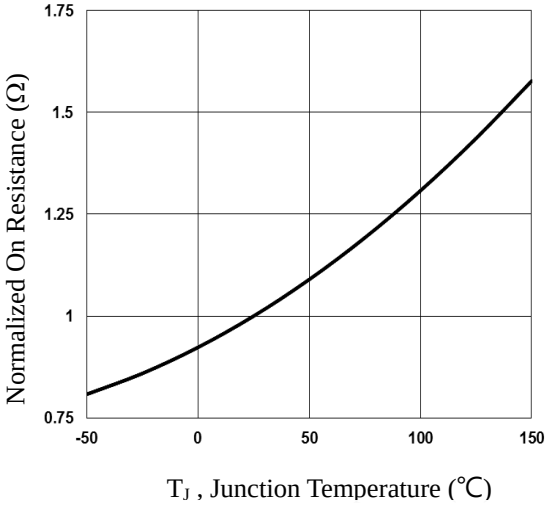


Fig.2 Normalized RDSON vs. T_J

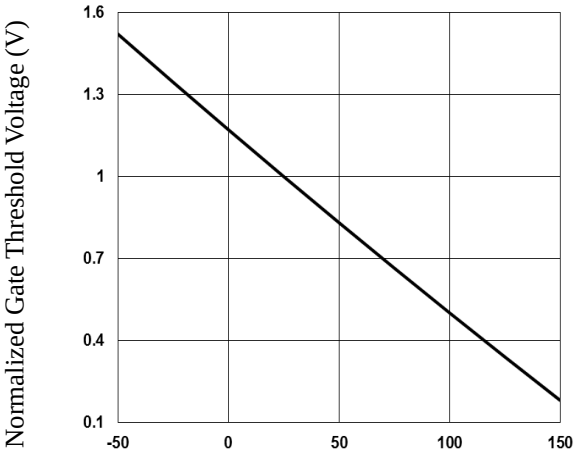


Fig.3 Normalized V_{th} vs. T_J

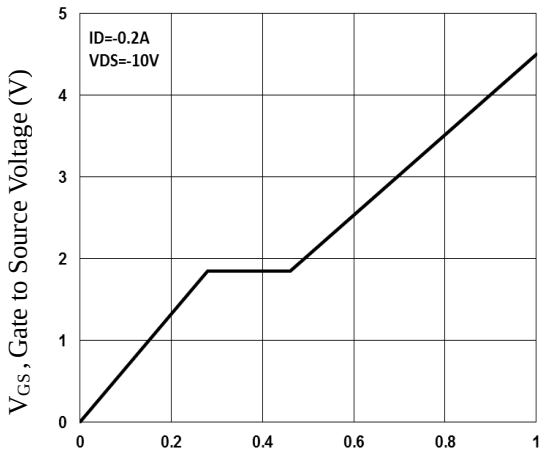


Fig.4 Gate Charge Waveform

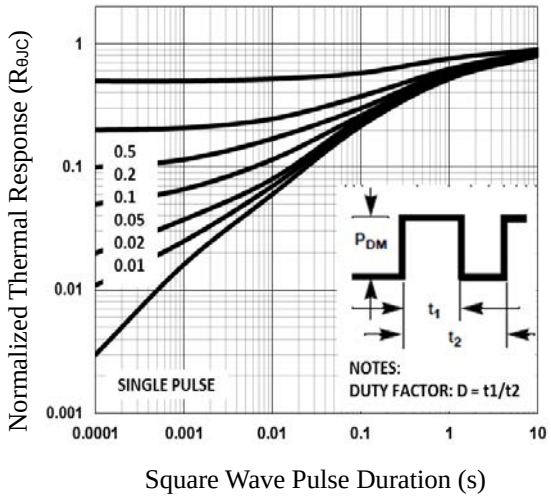


Fig.5 Normalized Transient Impedance

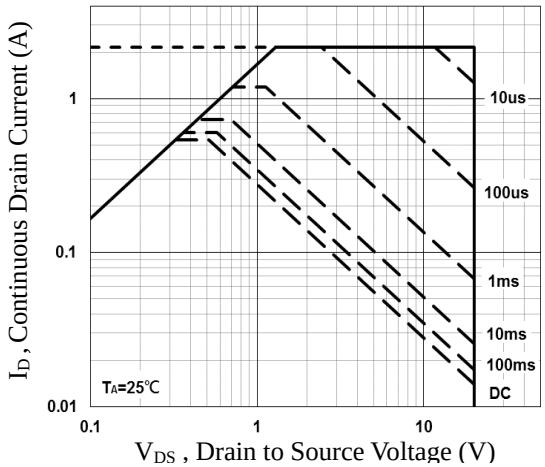
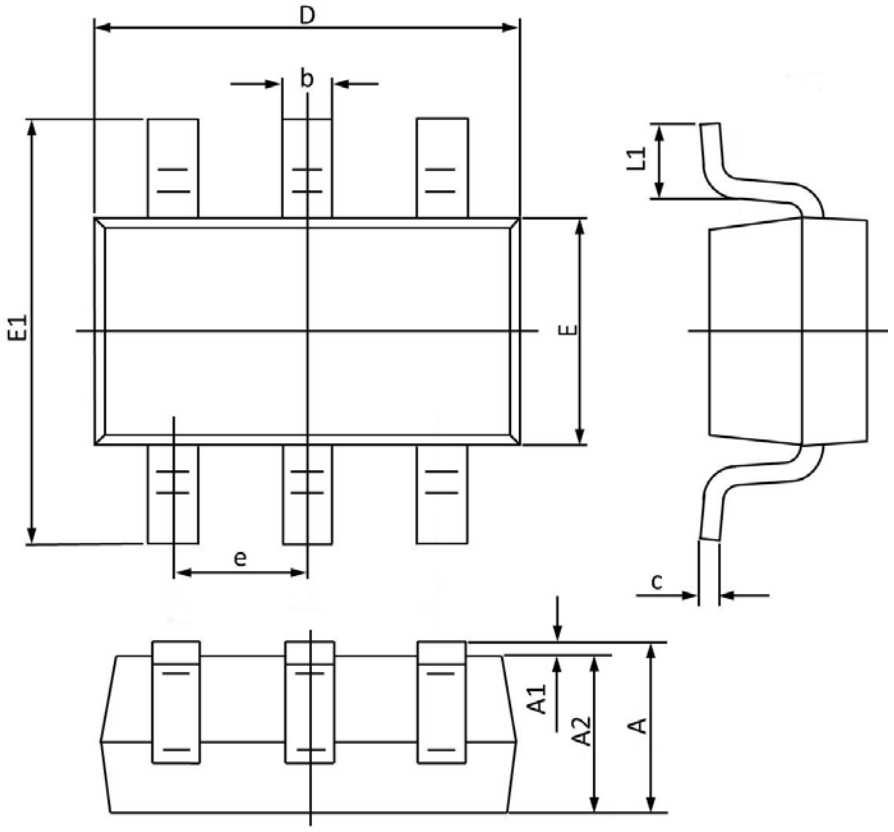


Fig.6 Maximum Safe Operation Area

PACKAGE OUTLINE & DIMENSIONS

YSE2219ZDW

SOT-363 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.330	0.100	0.013	0.004
c	0.250	0.100	0.010	0.004
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.400	1.800	0.094	0.071
e	0.65BSC		0.026BSC	
L1	0.350	0.100	0.014	0.004